

## High volume 5.6mm TO metal package laser diode “LU” series



### Introduction

Excelitas Technologies’ multi-epi 905 nm pulsed semiconductor lasers consists of a series of devices having up to four active lasing layers epitaxially grown on a single GaAs substrate chip. This multi-layer design multiplies the output power by the number of epi-layers.

The laser diode is epoxy mounted within a metal 5.6mm CD hermetic package, which is designed for high volume commercial and consumer applications where cost is a key driver in the system design.

This series of lasers comes in emitting cavity widths of 37.5, 75 and 225 $\mu$ m. Peak wavelength is centered near the maximum responsivity of most silicon photodiodes. The LU series lasers match especially well with devices from the Excelitas epi-APD family C30737.

### Key Features

- Multiplying the output power from a single epi-cavity chip with a small active area
- High reliability
- High volume hermetic metal 5.6mm TO package
- Multi epi-cavity Quantum well structure
- High peak pulsed power into aperture
- Excellent power stability with temperature
- RoHS Compliant

### Applications

- LIDAR
- Laser range finding
- Laser-based speed enforcement
- IR-illumination
- Laser skin therapy

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**Table 1: Maximum Ratings**

| Parameter                            | Symbol   | Min | Max  | Units |
|--------------------------------------|----------|-----|------|-------|
| Peak reverse voltage                 | $V_{RM}$ |     | 6    | V     |
| Pulse duration                       | $t_W$    |     | 100  | ns    |
| Duty factor                          | du       |     | 0.1  | %     |
| Storage temperature                  | $T_S$    | -55 | 105  | °C    |
| Operating temperature                | $T_{OP}$ | -55 | 85   | °C    |
| Soldering for 5 seconds (leads only) |          |     | +260 | °C    |

**Table 2: Generic Electro Optical Specifications at 23°C**

| Parameter                                                        | Symbol                   | Min | Typ  | Max | Units   |
|------------------------------------------------------------------|--------------------------|-----|------|-----|---------|
| Center wavelength of spectral envelope                           | $\lambda_c$              | 895 | 905  | 915 | nm      |
| Spectral bandwidth at 50% intensity points                       | $\Delta\lambda$          |     | 5    |     | nm      |
| Wavelength temperature coefficient                               | $\Delta\lambda/\Delta T$ |     | 0.25 |     | nm/°C   |
| Beam spread (50% peak intensity) parallel to junction plane      | $\Theta_{  }$            |     | 10   |     | degrees |
| Beam spread (50% peak intensity) perpendicular to junction plane | $\Theta_{\perp}$         |     | 25   |     | degrees |

**Table 3: Electro-optical characteristics - Typical electro-optical characteristics, @100ns, 1 kHz**

| Characteristics                                  | Symbol   | LDPGAU1S03 | LTPGAU1S1.5 | LTPGAU1S03 | LTPGAU1S09 | LQPGAU1S1.5 | LQPGAU1S03 | Units  |
|--------------------------------------------------|----------|------------|-------------|------------|------------|-------------|------------|--------|
| # of Emitting stripes / cavities                 |          | 2          | 3           | 3          | 3          | 4           | 4          |        |
| Emitting area                                    |          | 75x5       | 37.5X10     | 75x10      | 225x10     | 37.5x15     | 75x15      | μm     |
| Optical Power at $i_F$<br>- Minimum<br>- Typical | $P_o$    | 14<br>16   | 8<br>9.5    | 21<br>24   | 70<br>75   | 9.5<br>11   | 25<br>30   | W<br>W |
| Maximum Peak forward Current (100ns 1KHz)        | $i_F$    | 10         | 5           | 10         | 30         | 5           | 10         | A      |
| Typical Lasing threshold current                 | $i_{th}$ | 0.75       | 0.5         | 0.75       | 1.75       | 0.5         | 0.75       | A      |
| Typical Forward voltage <sup>1</sup> at $i_F$    | $V_F$    | 6.67       | 9.25        | 10.6       | 12.8       | 13          | 14.7       | V      |
| Typical Series Resistance                        | $R_S$    | 0.257      | 0.55        | 0.41       | 0.21       | 0.685       | 0.52       | Ω      |
| Typical Band gap Voltage Drop                    | $V_g$    | 4.1        | 6.5         | 6.5        | 6.5        | 9.5         | 9.5        | V      |

**Note 1:** As estimated by  $V_F = R_S i_F + V_g$ .

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## Electro-Optical Characteristics

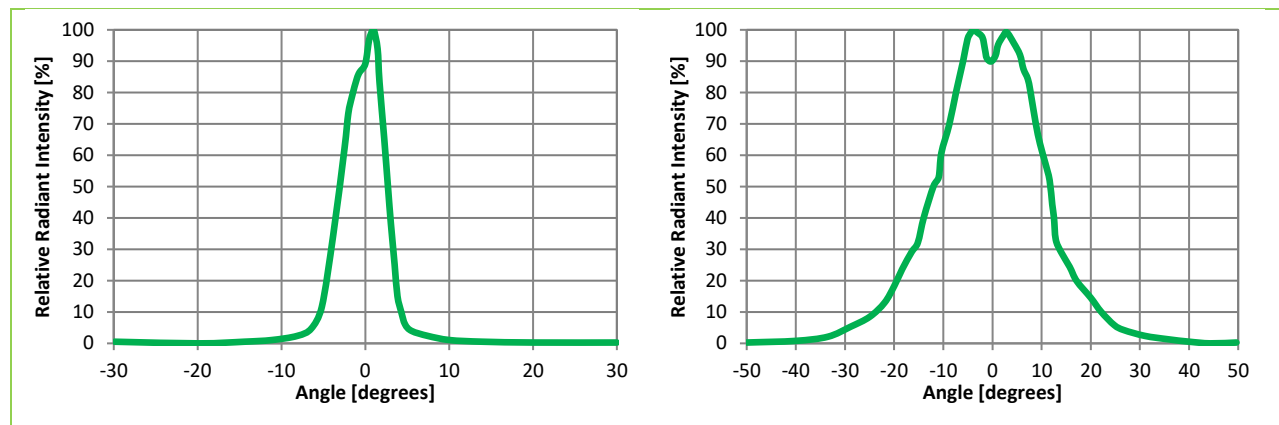
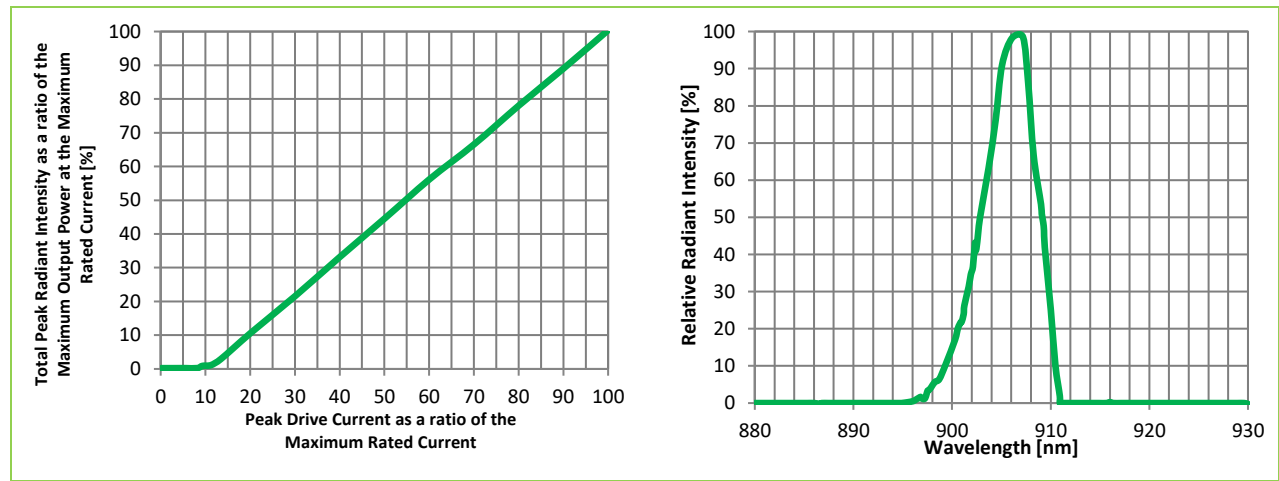
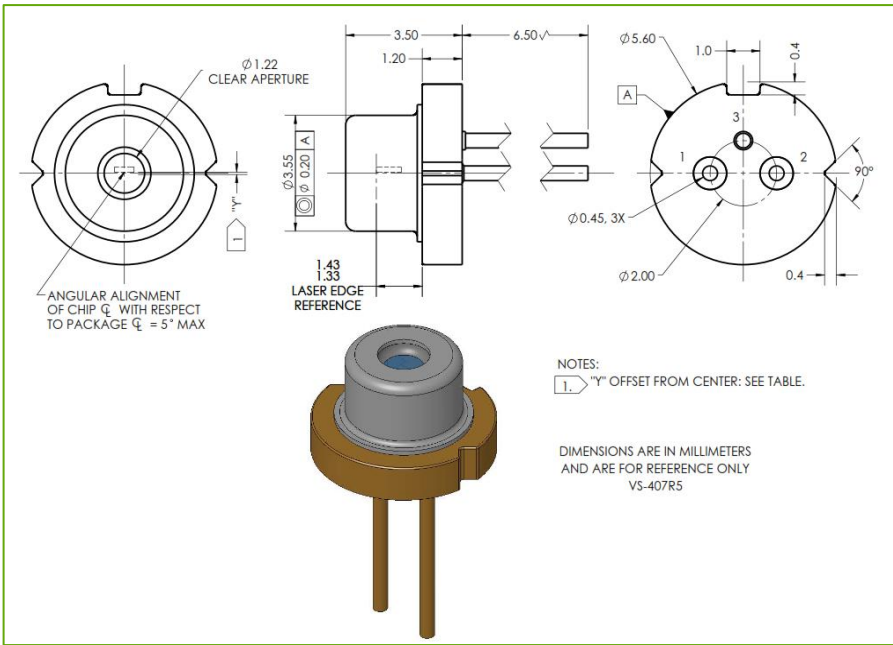


Figure 4: Package Mechanical Dimensions



### Package LU:

Pin-out

1. LD Anode (+)
2. NC
3. LD Cathode (-)

Package inductance: 5nH

| CHIP POSITION CENTER OFFSET |     |        |        |        |      |
|-----------------------------|-----|--------|--------|--------|------|
| Part#                       | DIM | Min    | Typ    | Max    | Unit |
| LDPGAU****                  | X   | -0.050 | 0.000  | 0.050  | mm   |
| LTPGAU****                  |     |        |        |        |      |
| LQPGAU****                  |     |        |        |        |      |
| LDPGAU****                  | Y   | -0.130 | -0.080 | -0.030 | mm   |
| LTPGAU****                  |     |        |        |        |      |
| LQPGAU****                  |     | -0.080 | -0.030 | 0.020  | mm   |

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## Operating Conditions

The laser is operated by pulsing current in the forward bias direction.

The Excelitas warranty applies only to devices operated within the maximum rating, as specified. Exceeding these conditions is likely to cause permanent “burn off” damage to the laser facet and consequently a significant reduction in optical power. Operating the devices at increased duty cycles will ultimately and irreparably damage the crystal structure due to internal heating effects.

Diodes are static sensitive and suitable precautions should be taken when removing the units from their antistatic containers. Circuits should be designed to protect the diodes from high current and reverse voltage transients. Voltages exceeding the reverse breakdown of the semiconductor junction are particularly damaging and have been shown to cause degradation of power output.

Although the devices will continue to perform well at elevated temperatures for some thousands of hours, defect mechanisms are accelerated. Optimum long term reliability will be attained with the semiconductor at or below room temperature.

Adequate heat sinking should be employed when operated at maximum duty factor.

## Warranty

A standard 12-month warranty following shipment applies. Any warranty is null and void if the package window has been opened.

## For Your Safety

Laser Radiation:

Under operation, these devices produce invisible electromagnetic radiation that may be harmful to the human eye. To ensure that these laser components meet the requirements of Class IIIb laser products, they must not be operated outside their maximum ratings. Power supplies used with these components must be such that the maximum peak forward current cannot be exceeded. It is the responsibility of the user incorporating a laser into a system to certify the Class of use and ensure that it meets the requirements of the ANSI or appropriate authority.

Further details can be obtained in the following publications:

**21CFR 1040.10** – “Performance Standards for Light Emitting Products (Laser Products)”

**ANSI Z136.1** – “American National Standard for Safe Use of lasers”

**IEC 60825-1** – “Safety of Laser Products”

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## RoHS Compliance

This series of laser diodes are designed and built to be fully compliant with the European Union Directive 2011/65/EU – Restriction of the use of certain Hazardous Substances (RoHS) in Electrical and Electronic equipment.



## About Excelitas Technologies

Excelitas Technologies is a global technology leader focused on delivering innovative, customized solutions to meet the lighting, detection and other high-performance technology needs of OEM customers.

Excelitas has a long and rich history of serving our OEM customer base with optoelectronic sensors and modules for more than 45 years beginning with PerkinElmer, EG&G, and RCA. The constant throughout has been our innovation and commitment to delivering the highest quality solutions to our customers worldwide.

From aerospace and defense to analytical instrumentation, clinical diagnostics, medical, industrial, and safety and security applications, Excelitas Technologies is committed to enabling our customers' success in their specialty end-markets. Excelitas Technologies has approximately 5,000 employees in North America, Europe and Asia, serving customers across the world.

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